

Title (en)  
AMORPHOUS OR MICROCRYSTALLINE ALLOYS BASED ON ALUMINIUM

Publication  
**EP 0100287 B1 19861112 (FR)**

Application  
**EP 83420113 A 19830704**

Priority  
FR 8212404 A 19820706

Abstract (en)  
[origin: US4595429A] The present invention relates to substantially amorphous or microcrystalline aluminium-base alloys. Such alloys are of the following chemical composition:  $\text{AlaMbM'cXdYe}$  in which:  $50 \leq a \leq 95$  atom % M representing one or more metals of the group Mn, Ni, Cu, Zr, Ti, V, Cr, Fe and Co with:  $0 \leq b \leq 40$  atom % M' representing Mo and/or W with:  $0 \leq c \leq 15$  atom % X representing one or more elements of the group Ca, Li, Mg, Ge, Si and Zn, with:  $0 \leq d \leq 20$  atom % Y representing the inevitable production impurities such as O, N, C, H, He, Ga, etc . . . , the proportion of which does not exceed 3 atom %. The alloys according to the invention can be produced by means of known methods in the form of wires, strips, bands, sheets or powders in the amorphous or microcrystallized state, the grain size of which is less than 1000 nm, preferably 100 nm. They may be used either directly or as means for reinforcing other materials, or as surface coatings which are resistant to corrosion or wear.

IPC 1-7  
**C22C 21/00**

IPC 8 full level  
**C22C 21/00** (2006.01); **C22C 45/08** (2006.01)

CPC (source: EP US)  
**C22C 45/08** (2013.01 - EP US)

Citation (examination)  

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Designated contracting state (EPC)  
AT BE CH DE GB IT LI NL SE

DOCDB simple family (publication)  
**EP 0100287 A1 19840208; EP 0100287 B1 19861112**; AT E23565 T1 19861115; CA 1214665 A 19861202; DE 3367622 D1 19870102; DK 163883 B 19920413; DK 163883 C 19920914; DK 310083 A 19840107; DK 310083 D0 19830705; FR 2529909 A1 19840113; FR 2529909 B1 19861212; IL 69123 A0 19831031; IL 69123 A 19870331; JP H0116899 B2 19890328; JP S5920442 A 19840202; NO 160862 B 19890227; NO 160862 C 19890607; NO 832458 L 19840109; US 4595429 A 19860617; US 4710246 A 19871201

DOCDB simple family (application)  
**EP 83420113 A 19830704**; AT 83420113 T 19830704; CA 431776 A 19830705; DE 3367622 T 19830704; DK 310083 A 19830705; FR 8212404 A 19820706; IL 6912383 A 19830630; JP 12147083 A 19830704; NO 832458 A 19830705; US 50699383 A 19830623; US 65516784 A 19840927